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March 2013

FQP17P06 P-Channel QFET® MOSFET

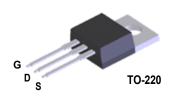
- 60 V, - 17 A, 120 $m\Omega$

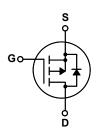
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- - 17 A, 60 V, $R_{DS(on)}$ = 120 m Ω (Max.) @ V_{GS} = 10 V, ID = 8.5 A
- Low Gate Charge (Typ.21 nC)
- Low Crss (Typ. 80 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			FQP17P06	Unit
V _{DSS}	Drain-Source Voltage		-60	V	
I _D	Drain Current - Continuous (T _C = 25°C)		-17	Α	
		- Continuous (T _C = 10	0°C)	-12	А
I _{DM}	Drain Current	- Pulsed	(Note 1)	-68	А
V_{GSS}	Gate-Source Vo	ce Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	300	mJ
I _{AR}	Avalanche Curr	valanche Current		-17	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	7.9	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	-7.0	V/ns
P _D	Power Dissipation (T _C = 25°C)			79	W
	- Derate above 25°C			0.53	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FQP17P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.9	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		-0.06		V/°C
I _{DSS}	7 0 1 1/1 5 1 0 1	V _{DS} = -60 V, V _{GS} = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = -48 V, T _C = 150°C			-10	μА
I _{GSSF}	Gate-Body Leakage Current, Forward V _{GS} = -25 V, V _{DS} = 0 V				-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse V _{GS} = 25 V, V _{DS} = 0 V				100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	tic Drain-Source $V_{CS} = -10 \text{ V. } I_D = -8.5 \text{ A}$		0.094	0.12	Ω
9 _{FS}	Forward Transconductance $V_{DS} = -30 \text{ V}, I_D = -8.5 \text{ A}$			9.3		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = -25 V, V _{GS} = 0 V,		690	900	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		325	420	pF
C _{rss}	Reverse Transfer Capacitance			80	105	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V - 30 V I - 8 5 A		13	35	ns
t _r	Turn-On Rise Time	$V_{DD} = -30 \text{ V}, I_{D} = -8.5 \text{ A},$ $R_{G} = 25 \Omega$		100	210	ns
t _{d(off)}	Turn-Off Delay Time	116 - 20 32		22	55	ns
t _f	Turn-Off Fall Time	(Note 4)		60	130	ns
Qg	Total Gate Charge	V _{DS} = -48 V, I _D = -17 A,		21	27	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		4.2		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		10		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-17	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				-68	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -17 A			-4.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -17 A,		92		ns
Q _{rr}	Reverse Recovery Charge dI _F / dt = 100 A/μs			0.32		μС

Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 1.2mH, I_{AS} = -17A, V_{DD} = -25V, R_G = 25 Ω , Starting T_J = 25°C 3. $_{SD} \le$ -17A, di/dt \le 300A/µs, V_{DD} \le BV_{DSS}, Starting T_J = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

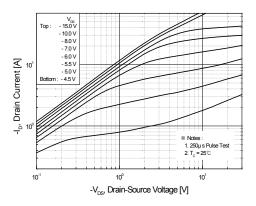


Figure 1. On-Region Characteristics

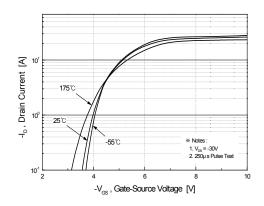


Figure 2. Transfer Characteristics

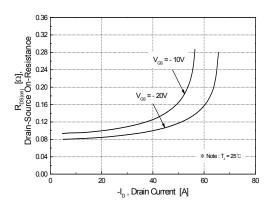


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

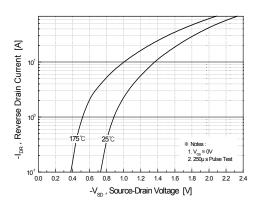


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

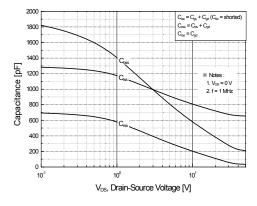


Figure 5. Capacitance Characteristics

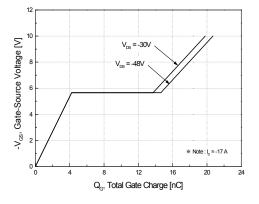
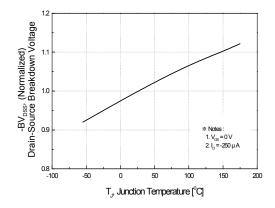


Figure 6. Gate Charge Characteristics

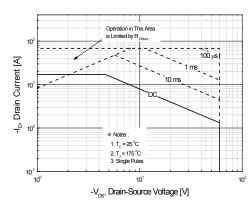
Typical Characteristics (Continued)



2.5 (Normalized) 1.5 (Normalized) 1.5 (Normalized) 1.5 (Normalized) 1.5 (Normalized) 1.5 (Normalized) 1.5 (Normalized) 1.7 (N

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



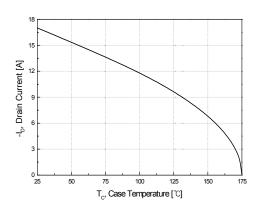


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

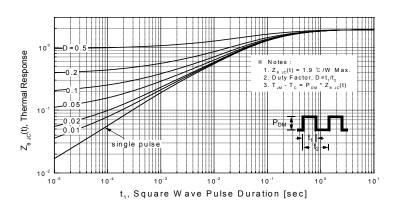
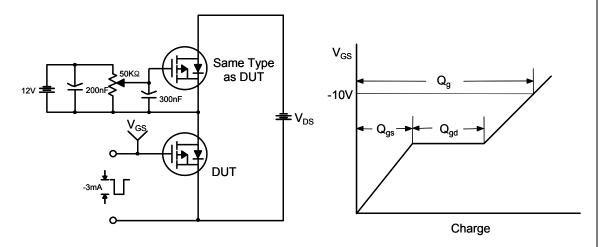
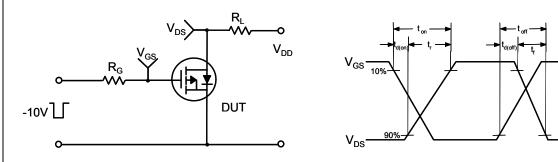


Figure 11. Transient Thermal Response Curve

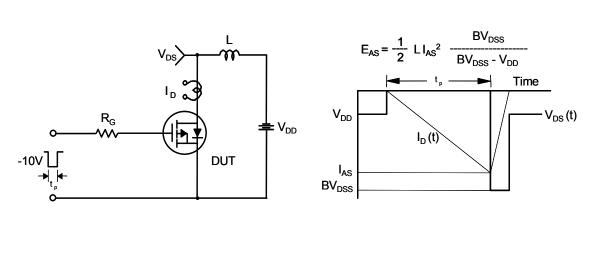
Gate Charge Test Circuit & Waveform



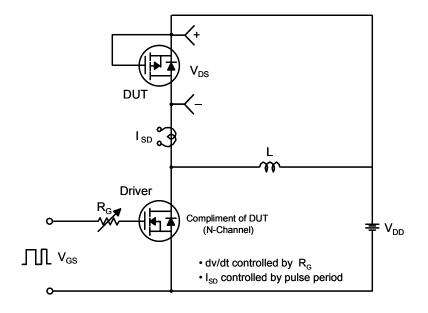
Resistive Switching Test Circuit & Waveforms

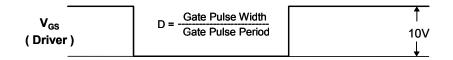


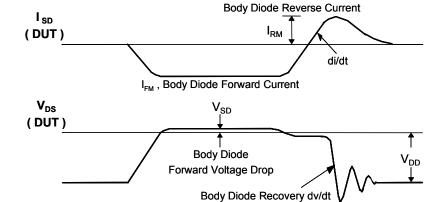
Unclamped Inductive Switching Test Circuit & Waveforms

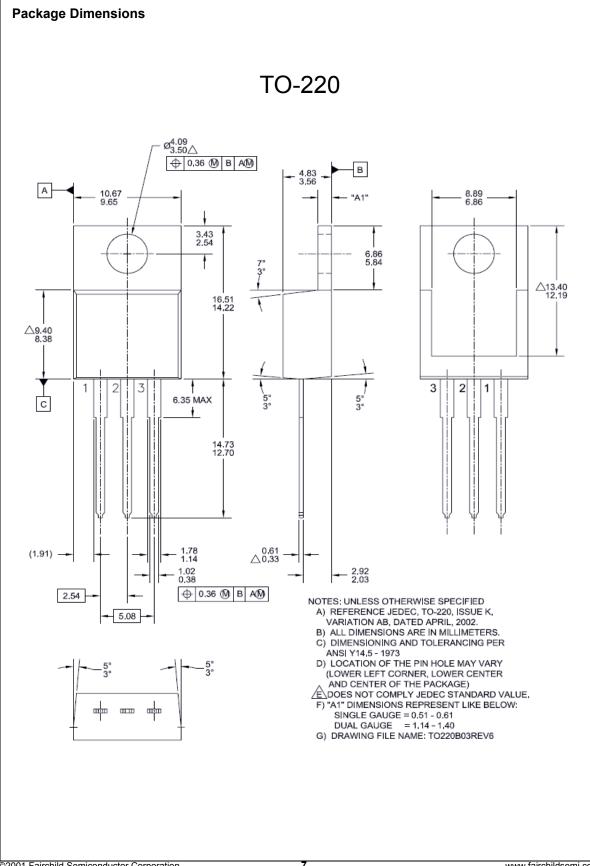


Peak Diode Recovery dv/dt Test Circuit & Waveforms













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105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

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